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Sheet 1 of 2

<b>FORM PTO-1449</b> <b>U.S. DEPARTMENT OF COMMERCE</b> <b>PATENT AND TRADEMARK OFFICE</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)	<b>ATTY. DOCKET NO.</b> 9138-0064(CIP)	<b>SERIAL NO</b> 09/981.024
	<b>APPLICANT</b> Tsong, et al.	
	<b>FILING DATE</b> October 16, 2001	<b>GROUP</b> 1765

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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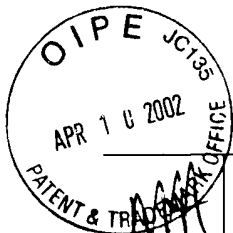
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**FOREIGN PATENT DOCUMENTS**

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
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**OTHER DOCUMENTS (Including Author, Title, Date Pertinent Pages, Etc.)**

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MA	Morkoc, et al., Journal of Applied Physics, "Large-band-gap SiC, III-V Nitride, and II-VI ZnSe-based Semiconductor Device Technologies", Vol. 76, pgs. 1363-1398 (1994)
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MA	Ruh, et al., Journal of The American Ceramic Society, "Composition and Properties of Hot-Pressed SiC-AIN Solid Solutions", Vol. 65, pgs. 260-265 (1982)
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<del>MAA</del>	Kern, et al., Journal of Materials Research, "Solid Solutions of AlN and SiC Grown by Plasma-assisted, Gas-source Molecular Beam Epitaxy, Vol. 8, No. 7, pgs. 1477-1480 (1993)
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<del>MAA</del>	Jenkins, et al., Journal of Crystal Growth, "Growth of Solid Solutions of Aluminum Nitride and Silicon Carbide by Metalorganic Chemical Vapor Deposition", Vol. 128, Nos. 1-4, pgs. 375-378 (1993)
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<del>MAA</del>	MacDiarmid, Journal of Inorganic and Nuclear Chemistry, "Pseudo-halogen Derivatives of Monosilane", Vol. 2, No. 2, pgs. 88-94 (1956)
<del>MAA</del>	Goldfarb, The Journal of Chemical Physics, "Infrared Spectrum and Structure of Germynl Cyanide", Vol. 37, No. 3, pgs. 642-646 (1962)
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*Matthew Andersen*

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